

IN THE CLAIMS:

Claims 6, 13, 23 and 30 through 37 were previously cancelled. None of the claims have been amended herein. All of the pending claims are presented below. This listing of claims will replace all prior versions and listings of claims in the application. Please enter these claims as previously amended.

Listing of Claims:

1. (Original) A semiconductor circuit fuse, comprising:
an insulating substrate;
a refractory metal nitride layer disposed above the insulating substrate; and
a tungsten silicide layer disposed over the refractory metal nitride layer.
2. (Original) The semiconductor circuit fuse of claim 1, wherein the insulating substrate is an isolation region.
3. (Original) The semiconductor circuit fuse of claim 2, wherein the isolation region is a field oxide region.
4. (Original) The semiconductor circuit fuse of claim 3, wherein the field oxide region is disposed on a semiconductor substrate.
5. (Original) The semiconductor circuit fuse of claim 4, wherein the semiconductor substrate is a silicon wafer.
6. (Cancelled)

7. (Previously presented) The semiconductor circuit fuse of claim 1, wherein the refractory metal nitride layer and the tungsten silicide layer include a neck portion located between terminal portions.

8. (Original) The semiconductor circuit fuse of claim 7, wherein the neck portion is smaller in width than the terminal portions.

9. (Original) The semiconductor circuit fuse of claim 8, wherein the neck portion has a width within a range of about 0.2 to about 1 micron.

10. (Previously presented) The semiconductor circuit fuse of claim 9, wherein the width of the neck portion is about 0.35 micron.

11. (Original) The semiconductor circuit fuse of claim 9, wherein a length of the neck portion is within a range of about 1 to about 10 microns.

12. (Original) The semiconductor circuit fuse of claim 11, wherein the length of the neck portion is about 3.5 microns.

13. (Cancelled)

14. (Previously presented) A semiconductor circuit fuse, comprising:
an insulating substrate;
a refractory metal nitride layer disposed above the insulating substrate; and
a silicide layer disposed over the refractory metal nitride layer.

15. (Original) The semiconductor circuit fuse of claim 14, wherein the insulating substrate is an isolation region.

16. (Original) The semiconductor circuit fuse of claim 15, wherein the isolation region is a field oxide region.
17. (Original) The semiconductor circuit fuse of claim 16, wherein the field oxide region is disposed on a semiconductor substrate.
18. (Original) The semiconductor circuit fuse of claim 17, wherein the semiconductor substrate is a silicon wafer.
19. (Original) The semiconductor circuit fuse of claim 14, wherein the refractory metal nitride layer includes titanium.
20. (Original) The semiconductor circuit fuse of claim 14, wherein the refractory metal nitride layer comprises titanium nitride.
21. (Previously presented) The semiconductor circuit fuse of claim 14, wherein the silicide layer is selected from the group consisting of a metal, metal alloy and metal compound.
22. (Previously presented) The semiconductor circuit fuse of claim 14, wherein the silicide layer comprises tungsten silicide.
23. (Cancelled)
24. (Previously presented) The semiconductor circuit fuse of claim 14, wherein the refractory metal nitride layer and the silicide layer have a similar shape comprising a neck portion located between terminal portions.

25. (Original) The semiconductor circuit fuse of claim 24, wherein the neck portion is smaller in width than the terminal portions.

26. (Original) The semiconductor circuit fuse of claim 25, wherein the neck portion has a width within a range of about 0.2 to about 1 micron.

27. (Previously presented) The semiconductor circuit fuse of claim 26, wherein the width of the neck portion is about 0.35 micron.

28. (Original) The semiconductor circuit fuse of claim 27, wherein a length of the neck portion is within a range of about 1 to about 10 microns.

29. (Original) The semiconductor circuit fuse of claim 28, wherein the length of the neck portion is about 3.5 microns.

30.-37. (Cancelled)

38. (Previously presented) A semiconductor circuit fuse, comprising:
an insulating substrate;
a refractory metal nitride layer disposed above the insulating substrate; and
a tungsten silicide layer disposed over the refractory metal nitride layer, the refractory metal nitride layer and the tungsten silicide layer configured to a similar shape.

39. (Previously presented) A semiconductor circuit fuse, comprising:
an insulating substrate;
a refractory metal nitride layer disposed above the insulating substrate; and
a silicide layer disposed over the refractory metal nitride layer, the refractory metal nitride layer and the silicide layer configured to a similar shape..